NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI J02015A** is Designed for High Power Class C Amplifier in, 225 to 400 MHz Military Communication Equipment.

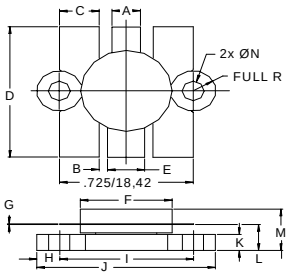
FEATURES:

- Internal Input Matching Network
- P_G = 8.4 dB at 70 W/400 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	220 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.25 °C/W

PACKAGE STYLE .500 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M		.285 / 7.24
N	.120 / 3.05	.135 / 3.43

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	30			V
BV_{CES}	I_C = 50 mA	60			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CBO}	V_{CB} = 30 V			5.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 2.0 A	20		80	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz			80	pF
P_G	V_{CC} = 28 V P_{OUT} = 70 W f = 400 MHz	8.4			dB
η_D			60		%

Specifications are subject to change without notice.